

**Performance**

- Frequency: 13.1-13.3GHz
- Gain: 6dB
- Output Power: 51dBm (Typ.)
- PAE: 28% (Typ.)
- Bias: 28V/1.2A
- Hermetically Sealed Package
- Size: 24.0\*17.4\*4.4mm

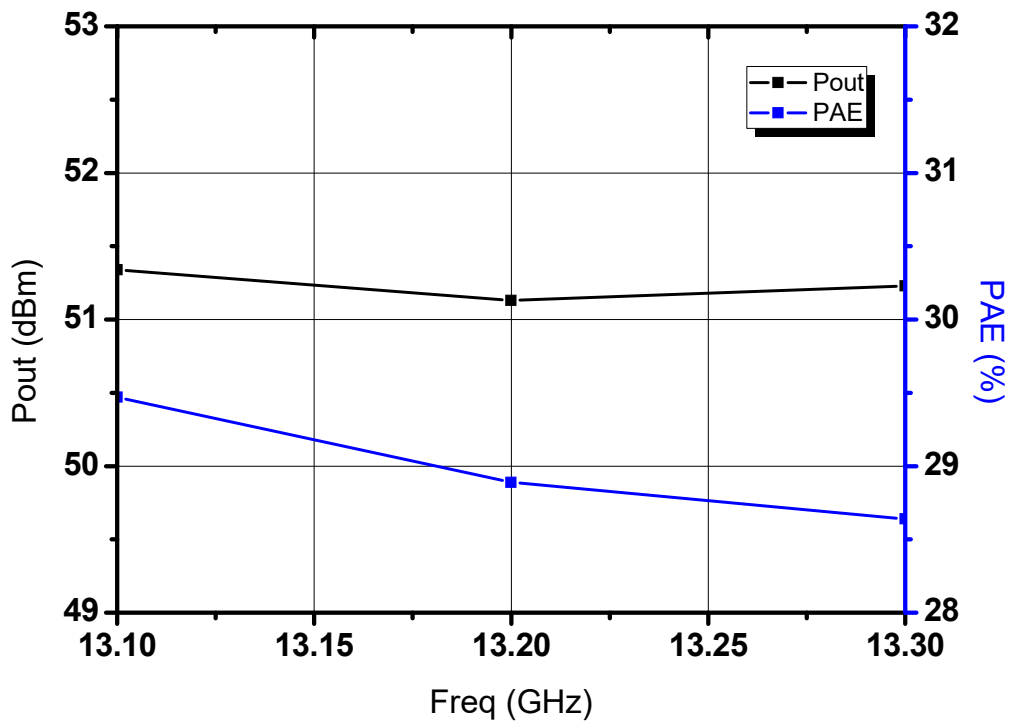


**Electrical Specifications (Ta=+25°C, 50Ω system)**

| Symbol           | Parameter              | Test Condition  | Min  | Typical | Max  | Unit |
|------------------|------------------------|---|------|---------|------|------|
| P <sub>out</sub> | Output Power           | V <sub>d</sub> =28V, I <sub>d</sub> =1.2A<br>Freq: 13.1-13.3GHz<br>100us, 10% D.C |      | 51      | -    | dBm  |
| G <sub>p</sub>   | Power Gain             |   | -    | 6       | -    | dB   |
| η <sub>add</sub> | Power Added Efficiency |   | -    | 28      | -    | %    |
| ΔG <sub>p</sub>  | Gain Flatness          |   | -0.8 | -       | +0.8 | dB   |

**Test Curves (Ta=+25°C)**

**Output Power and PAE**

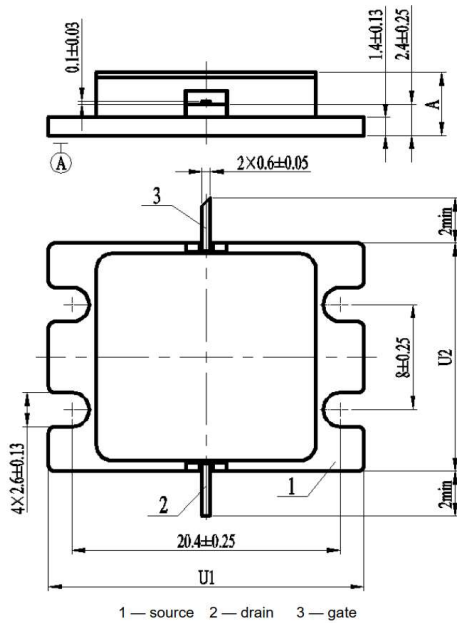


**Absolute Max Ratings (TA=25°C)**

| Symbol | Parameter             | Value     | Remark              |
|--------|-----------------------|-----------|---------------------|
| Vds    | Drain Bias Voltage    | 40V       |                     |
| Vgs    | Gate Bias Voltage     | -5V       |                     |
| Pd     | DC Power Consumption  | 125W      | 25°C                |
| Tch    | Channel Temperature   | 225°C     |                     |
| Tm     | Sintering Temperature | 300°C     | 1min, N2 protection |
| Tstg   | Storage Temperature   | -55~175°C |                     |

Exceeding any one or combination of these limits may cause permanent damage.

**Outline Size**



| Symbol | Min  | Max  |
|--------|------|------|
| U1     | 23.8 | 24.2 |
| U2     | 17.2 | 17.6 |
| A      |      | 5.2  |